

$$N_a = 10^{18} \text{ cm}^{-3}$$

$$N_d = 5 \cdot 10^{15} \text{ cm}^{-3}$$

and  $n_i = 10^{10} \text{ cm}^{-3}$  (in Si)

a) Fermi levels in the n region:

$$\Delta E_n = E_{Fn} - E_{Fi} = k_B T \ln\left(\frac{N_d}{n_i}\right) \approx \underline{\underline{0.340 \text{ eV}}} \text{ above intrinsic level}$$

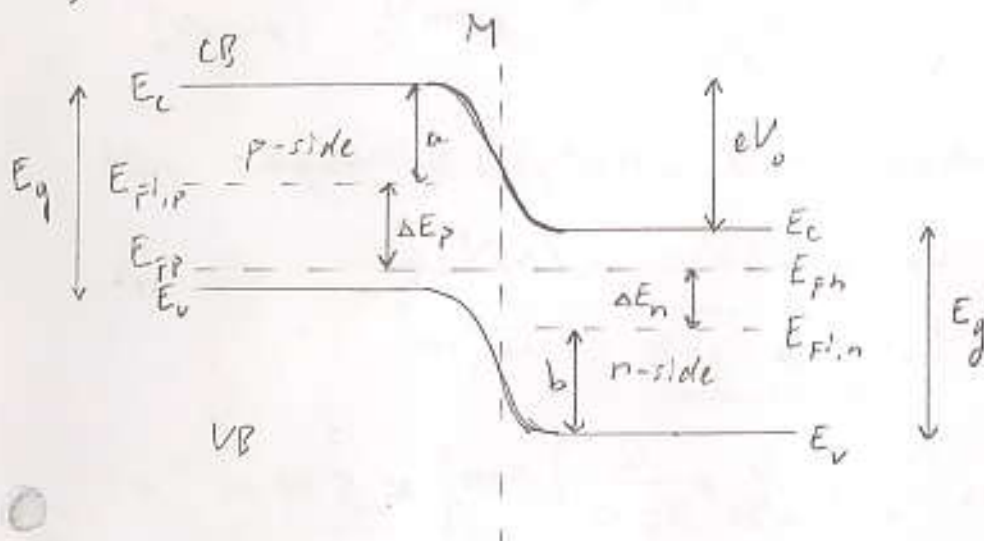
at room temp.

in the p-region

$$\Delta E_p = E_{Fp} - E_{Fi} = -k_B T \ln\left(\frac{N_a}{n_i}\right) \approx \underline{\underline{-0.480 \text{ eV}}} \text{ below intrinsic level}$$

at room temp.

b) Fermi level position is continuous



From geometric consideration:

$$eV_0 + E_g = a + \Delta E_p + \Delta E_n + b \quad (a+b = E_g)$$

$$eV_0 + E_g = E_g + \Delta E_p + \Delta E_n$$

$$eV_0 = \Delta E_p + \Delta E_n \approx \underline{\underline{0.820 \text{ eV}}}$$

c)  $eV_0 = k_B T \ln\left(\frac{N_a N_d}{n_i^2}\right) \approx \underline{\underline{0.820 \text{ eV}}}$  same as above

2) Shockley long diode equation

$$J = \left( \frac{D_p}{L_p N_d} + \frac{D_n}{L_n N_a} \right) e n_i^2 \left[ \exp\left(\frac{eV}{k_B T}\right) - 1 \right]$$

Current:

$$\begin{aligned} I = JA &= \left( \frac{D_p}{L_p N_d} + \frac{D_n}{L_n N_a} \right) A e n_i^2 \left[ \exp\left(\frac{eV}{k_B T}\right) - 1 \right] \\ &= I_0 \left[ \exp\left(\frac{eV}{k_B T}\right) - 1 \right] \end{aligned}$$

Constant  $I_0$ : Minority carrier diffusion coefficients

$$D_p = \frac{k_B T}{e} \mu_p \approx 116,55 \text{ cm}^2/\text{s} \quad (\text{n-side})$$

$$D_n = \frac{k_B T}{e} \mu_n \approx 18,13 \text{ cm}^2/\text{s} \quad (\text{p-side})$$

Minority carrier diffusion lengths

$$L_p = \sqrt{D_p \tau_p} \approx 34,1 \cdot 10^{-3} \text{ cm}$$

$$L_n = \sqrt{D_n \tau_n} \approx 1,3 \cdot 10^{-3} \text{ cm}$$

$$e = 1,6 \cdot 10^{-19} \text{ C}$$

$$\text{Unit: C/s} = \text{A}$$

$$\Rightarrow I_0 = \left( \frac{D_p}{L_p N_d} + \frac{D_n}{L_n N_a} \right) A e n_i^2 \approx 5,68 \cdot 10^{-15} \text{ A}$$

Diffusion current: at  $V = 0,5 \text{ V}$ :

$$I = I_0 \left[ \exp\left(\frac{0,5 \text{ eV}}{0,0257 \text{ eV}}\right) - 1 \right] \approx \underline{\underline{1,37 \cdot 10^{-6} \text{ A}}}$$

at  $V = -0,5 \text{ V}$

$$I = I_0 \left[ \exp\left(\frac{-0,5 \text{ eV}}{0,0257 \text{ eV}}\right) - 1 \right] \approx \underline{\underline{-5,68 \cdot 10^{-15} \text{ A}}}$$

Electron effective mass in GaAs

$$m_e^* = 0,067 m_e, \quad m_e = 9,1 \cdot 10^{-31} \text{ kg}$$

Thermal velocity of electrons in CB of a nondegenerately doped GaAs at 300K.

Electron wanders around the crystal with an average kinetic energy of  $\frac{3}{2} k_B T$ .

$$\Rightarrow \frac{1}{2} m_e^* v_{th}^2 = \frac{3}{2} k_B T$$

$$v_{th} = \sqrt{\frac{3 k_B T}{m_e^*}}, \quad k_B = 1,38 \cdot 10^{-23} \text{ J/K}$$

$$\approx \underline{\underline{4,51 \cdot 10^5 \text{ m/s}}} \quad \underline{\underline{\text{Fast}}}$$

Mean free time between electron scattering events:

$$\mu_e = \frac{e \tau_e}{m_e^*} \Leftrightarrow \tau_e = \frac{\mu_e m_e^*}{e}$$

$$\approx \underline{\underline{3,24 \cdot 10^{-13} \text{ s}}} \quad \underline{\underline{\text{Short time}}}$$

$\mu_e = 8500 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$   
 $e = 1,6 \cdot 10^{-19} \text{ C}$

$$\text{Unit: } \frac{\text{m}^2}{\text{Vs}} \cdot \text{kg} \cdot \frac{1}{\text{C}} = \frac{\text{m}^2 \cdot \text{kg}}{\text{Vs}} \cdot \frac{1}{\text{As}} = \frac{\text{Nm}}{\text{VA}} = \frac{\text{Nm}}{\text{W}} = \frac{\text{Nm}}{\text{Nm/s}} \text{ s} = \text{s}$$

Drift velocity of CB electrons in an applied E-field of  $10^5 \text{ V/m}$ :

$$v_d = \mu_e E = \underline{\underline{8,5 \cdot 10^4 \text{ m/s}}} \quad \text{order of magnitude lower than } v_{th}$$

4) Photon energy:  $E = h\nu = h \frac{c}{\lambda} \Rightarrow \lambda = \frac{hc}{E}$

Differential of  $\lambda$  with respect to  $E$ :

$$\frac{d\lambda}{dE} = - \frac{hc}{E^2} = - \frac{hc}{\left(\frac{hc}{\lambda}\right)^2} = - \frac{\lambda^2}{hc}$$

Sign does not matter for spreading

$$\Rightarrow \left| \frac{d\lambda}{dE} \right| \approx \frac{\Delta\lambda}{\Delta E} \quad \text{linearity assumed}$$

where  $\Delta E \approx 3k_B T$ .

$$\Rightarrow \frac{\Delta\lambda}{\Delta E} \approx \frac{\lambda^2}{hc}$$

$$\Delta\lambda \approx \frac{\lambda^2}{hc} \Delta E \approx \lambda^2 \frac{3k_B T}{hc} \quad \square$$

5)  $E_g = 1.42 \text{ eV}$ ,  $T = 300 \text{ K}$ ,  $h = 4.135 \cdot 10^{-15} \text{ eVs}$

$$\lambda = \frac{hc}{E_g}$$

$E_g$  depends on  $T$

$$\Rightarrow \frac{d\lambda}{dT} = - \frac{hc}{E_g^2} \frac{dE_g}{dT}$$

Assuming linearity we have  $\frac{d\lambda}{dT} \approx \frac{\Delta\lambda}{\Delta T}$

$$\Rightarrow \frac{\Delta\lambda}{\Delta T} \approx - \frac{hc}{E_g^2} \frac{dE_g}{dT}$$

$$\Delta\lambda \approx - \frac{hc}{E_g^2} \frac{dE_g}{dT} \Delta T$$

$$\approx \underline{\underline{2.8 \text{ nm}}}$$

$$\frac{dE_g}{dT} \approx -4.5 \cdot 10^{-4} \text{ eV/K}$$

$$\Delta T = 10^\circ \text{C} = 10 \text{ K}$$

) Width of the output spectrum is given by

$$\Delta E = m k_B T, \text{ where } m \text{ is a numerical constant}$$

a) Let's calculate  $\Delta \lambda$  in the same way than in prob. 4.

$$\lambda = \frac{hc}{E}$$

$$\frac{d\lambda}{dE} = -\frac{\lambda^2}{hc} \approx \frac{\Delta \lambda}{\Delta E} \Rightarrow \Delta \lambda = -\frac{\lambda^2}{hc} \Delta E = \underline{\underline{(-) \lambda^2 \frac{m k_B T}{hc}}}$$

sign does not matter for width

b) Plot the values  $\Delta \lambda$  as a function of  $\lambda$ .

Fit a parabolic function  $y = a \lambda^2$  to the data set. Fit results into a fit parameter

$$a = \frac{m k_B T}{hc} \approx (6,57 \pm 0,32) \cdot 10^4 \text{ 1/m}, \text{ 95\% confidence level}$$

where  $k_B T$  is assumed to be in room temp. and equals 0,0259 eV.

$$h = 4,135 \cdot 10^{-15} \text{ eV} \cdot \text{s} \quad \text{and} \quad c = 3 \cdot 10^8 \text{ m/s}$$

$$\Rightarrow m = \frac{ahc}{k_B T} \approx \underline{\underline{3,15 \pm 0,16}}, \text{ at 95\% confidence level}$$



